Reg. No .....

Name .....

25P2036

## M. Sc. DEGREE END SEMESTER EXAMINATION - APRIL 2025

## **SEMESTER 2 : PHYSICS**

COURSE : 24P2PHYT07 : CONDENSED MATTER PHYSICS

(For Regular 2024 Admission)

Time : Three Hours

Max. Weights: 30

|     | PART A   | -           |
|-----|--|-------------|
|     | Answer any 8 questions   | Weight: 1   |
| 1.  | Give drawbacks of the Debye model?   | (U)         |
| 2.  | What is meant by an extrinsic semiconductor?   | (A)         |
| 3.  | What is the normal scattering process of a photon?   | (U)         |
| 4.  | What are Fullerenes?   | (A)         |
| 5.  | What are antiferromagnetic materials?  | (A)         |
| 6.  | What is meant by Optical mode of wave propagation in linear diatomic<br>crystal  | (U)         |
| 7.  | Define the terms, mean free path and relaxation time. Obtain the expressions for both.   | (A)         |
| 8.  | Explain the concept of 'effective mass"?   | (U)         |
| 9.  | Give the expression for density of energy states in metals?  | (E)         |
| 10. | Draw (110) plane?  | (A)         |
|     |  | (1 x 8 = 8) |
|     | PART B   | Weights: 2  |
|     | Answer any 6 questions   | vveignts. Z |
| 11. | The applied magnetic field in copper is 10 <sup>6</sup> A/m. If the magnetic susceptibility of the copper is -0.8x10 <sup>-5</sup> , calculate the density and magnetization in copper.  | (A)         |
| 12. | A magnetizing field 100 A/m produces a flux density $4\pi x 10^{-3}$ T in a bar of material Calculate the relative permeability and susceptibility of the material?  | (A)         |
| 13. | Prove that the reciprocal lattice of a bcc lattice is an fcc lattice.  | (A)         |
| 14. | A uniform silver wire has a resistivity of 1.54x10 <sup>-8</sup> ohm.meter at room temperature. For an electric field along the wire of 1 V/cm, compute the  |             |
|     | average drift velocity of the electrons assuming that there are 5.8x10 <sup>28</sup> conduction electrons /m <sup>3</sup> . Also calculate the mobility and the relaxation time of the electron.   | (E)         |
| 15. | In a tetragonal lattice a=b=(1/2) nm and c=(1/3) nm. Determine the lattice spacing between (111) planes?   | (A)         |
| 16. | The intrinsic carrier density at room temperature in germanium is 2.37x10 <sup>19</sup> /m <sup>3</sup> . If the electron and hole mobilities are 0.38 and 0.18 m <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> , respectively. Calculate the resistivity of the intrinsic germanium. | (A)         |

| 17. | An intrinsic semiconductor material A has an energy gap 0.36 eV while<br>material B has an energy gap 0.72 eV. Compare the intrinsic carrier<br>densities in these two material at 300 K. Assume that the effective masses<br>of all the electrons and holes are equal to the free electron mass. | (A)          |
|-----|---|--------------|
| 18. | Calculate the intrinsic concentration of charge carriers at 300 K. Given that me* =0.12 m0, mh*=0.28 m0 and the energy gap of germanium at 300 K is 0.67 eV.  | (A)          |
|     |   | (2 x 6 = 12) |
|     | PART C  |              |
|     | Answer any 2 questions  | Weights: 5   |
| 19. | A particle of mass m is confined in a field free region between<br>impenetrable walls at x=0 and x=a. Find the stationary energy levels of the<br>particle. Discuss the physical significance of the wave function.   | (An)         |
| 20. | Briefly explain (i) Domain theory of ferromagnetism (ii) Explain magnetic hysteresis in the case of ferromagnets?   | (A)          |
| 21. | Discuss the thermal conductivity in crystalline material. Briefly discuss Normal and Umklapp process with the help of a diagram.  | (An)         |
| 22. | Discuss the extended, reduced and periodic zone scheme of Brillouin zone representations? Also briefly explain the construction of Brillouin zones in one and two dimensions?   | (An)         |
|     |   | (5 x 2 = 10) |

## OBE: Questions to Course Outcome Mapping

| СО | Course Outcome Description | CL | Questions | Total Wt. |  |
|----|----------------------------|----|-----------|-----------|--|
|----|----------------------------|----|-----------|-----------|--|

Cognitive Level (CL): Cr - CREATE; E - EVALUATE; An - ANALYZE; A - APPLY; U - UNDERSTAND; R - REMEMBER;